

Signals & Reconstruction

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- Interactions
 - Charged particles
 - X-rays
 - Photons
- Signals from moving charges
 - Drift and Diffusion
 - Weighting Field
 - Signals in Strip Detectors
- Reconstruction
 - Resolution with Binary Readout
 - Influence of Noise
 - Error of Centroid



INTERACTIONS

Interactions: Charged Particles

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- Described by famous Bethe-Bloch Formula
- Based on electrostatic interaction of moving charge with electrons in medium 10 Minimum Ionizing Particle

$$-\left\langle \frac{dE}{dx} \right\rangle = Kz^2 \frac{Z}{A\beta^2} \times \left[\frac{1}{2} \ln \frac{2m_e c^2 \beta^2 \gamma^2 T_{\text{max}}}{I^2} - \beta^2 + \cdots \right]$$

with
$$\frac{dE}{dx} : \text{Energy loss of the particle usually given in } \frac{eV}{g/cm^2}$$

 $K : 4\pi N_{\text{Av}} r_e^2 m_e c^2 = 0.307075 \text{ MeV cm}^2$
 $z : \text{Charge of the traversing particle in units of the electron}$
 $Z : \text{Atomic number of absorption medium (14 for silicon)}$
 $A : \text{Atomic mass of absorption medium (28 for silicon)}$
 $m_e c^2 : \text{Rest energy of the electron (0.511 MeV)}$
 $\beta : \text{Velocity of the traversing particle in units of the speed c}$
 $\gamma : \text{Lorentz factor } 1/\sqrt{1-\beta^2}$
 $I : \text{Mean excitation energy (137 eV for silicon)}.$

1000

10000

100

Proton momentum (GeV/c)

10

1.0

Electron Hole Pairs

- Average Energy required for creating one e-h-pair: ~3.6eV
- Use BB-Formula for mip for 300µm Si: ~3.5fC = 22.000 eh
- IfC = 6250 e!



Energy Distribution for Single Particles

- Ionization has statistical fluctuations
- Concept described by 'Landau **Distribution**', \exists better formulae
- Worst match for thin detectors
- Asymmetric: Average energy loss != most probable energy loss
- Conservative calculations use most probable value MPV
- One reason for large energy tail: Knock-on electrons 'δ rays'
- Often perpendicular to track



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Energy Loss in Silicon (500 MeV π)



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Summary

- In 300µm silicon, mips deposit ~ 3.5 fC ~ 22.000 eh
- Most probable energy < average energy</p>
- Asymmetry gets more pronounced for thin detectors
- Some hits depose a large energy.
 - This is caused by single fast electrons ('delta rays')
 - A large fraction of the energy is deposited 'at the side' → spatial resolution of such events is bad
- Note that charge gets smaller when shared among several electrodes.
 - For instance in the corner of 4 pixels: 22.000 / 4 = 5500 eh pairs
 - Readout must still be able to see this!

Electromagnetic radiation (γ = Photons, Gammas)

- Low E: Photo Effect
- Medium E: Compton Scatter $\gamma + e^- \rightarrow \gamma + e^-$
- High E:

- $\gamma \rightarrow e^+ e^-$ Pair Production
- γ → e⁻ (atom shell)



Measured cross section



Absorption Coefficients

- Gamma flux decreases with depth: $I = I_0 \exp(-t/\lambda)$
- λ often given in mass/unit area (g/cm²) which is more material independent





For mono energetic X-rays, the number of e/h pairs created is not constant



- The width is limited by the Fano Factor F ~ 0.1 (0.07...0.16)
- Calculation / measurement of F are difficult.

- It is impossible to measure 10keV with 10eV (3 eh) resolution!
- Germanium is slightly better, because only 2.9 eV are required per eh pair



Example: Spectrum of X-rays from ⁵⁵Fe

• ⁵⁵Fe \rightarrow (EC, 2.73a) \rightarrow ⁵⁵Mn (excited)

⁵⁵Mn emits a 5.90keV X-ray (K_α), 24%



• Spectrum with DEPFET, τ =10µs, noise = 1.6 e @ RT

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Visible Photons

- They are attenuated exponentially
- Photons must have at least E = hv = E_{gap} = 1.12eV to make e-h-pair → hard cutoff in IR (~1100 nm)
- Must take into account reflection at the surface (ε change)
- Example: 600µm silicon:



Absorption Coefficients for Visible Photons



Visible Photons

- Reflections at surface (Si, Passivation) can be reduced by anti reflex coatings (ARC)
 - Can be 'perfect' for a well defined wavelength
 - More difficult for wider spectra
- For short wavelength (UV), absorption is very high.
 If the detector has a 'dead layer' (e.g. thick implantations), this leads to significant losses
- For long wavelengths (IR), detectors must be thick

Multiple Scattering

- Several small scattering events lead to a (small) track deflection by an angle θ:
- This is a statistical process with average 0 and some rms value



- Material thickness measured in radiation lengths X_o
- This degrades track reconstruction → momentum error

When the particle transverses the detector it is deflected by many small angle scatters. The deflection is mainly caused by Coulomb interaction of the charged particle with the nuclei. For hadrons the strong interaction also gives a contribution. The scattering angle of the projectile after many interactions when leaving the detector follows roughly a Gaussian distribution [50] with an rms of

$$\theta_{\text{plane}}^{\text{rms}} = \frac{13.6 \,\text{MeV}}{\beta pc} z \sqrt{x/X_0} \left[1 + 0.038 \ln\left(x/X_0\right)\right]$$
(2.11)

where the angle θ is expressed in rad, the particle momentum p in MeV and the velocity β in units of the velocity of light c. The charge number of the projectile is z and x/X_0 is the thickness of the absorption medium in units Particle Data Book

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Why is $\sigma \propto \sqrt{\text{Thickness}}$ (roughly)?

• Assume $\sigma = f(x)$ (x = thickness)



 $\sigma_1 = f(D)$





MOTION OF ELECTRONS (AND HOLES)

What is 'Drift' ?

- Particles in a field
- Cars on a street
- 'Zorb' balls on a hill _

reach a limit velocity although the accelerating force remains



- This is because energy is dissipated by other mechanisms and is not available for acceleration any more
 - Acceleration stops when $E_{DISSIPATED}(v) = E_{FED_INTO_SYSTEM}$

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- Charges move in E-field with speed v = µ E
- µ is the mobility. It is different for electrons and holes:

$$\mu_{\rm n} = 1415 \pm 46 \, \frac{{
m cm}^2}{{
m V} \cdot {
m s}} ~\sim 140 \, \mu {
m m}^2$$
/ (V ns)
 $\mu_{\rm p} = ~480 \pm 17 \, \frac{{
m cm}^2}{{
m V} \cdot {
m s}}$

Many different numbers in literature...

Drift speed saturates at high field ('velocity saturation')

 u decreases ('mobility degradation')

μ decreases ('mobility degradation')



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When is drift speed reached ?

- Estimate how long it takes to accelerate an electron to full drift velocity:
 - i.e. assuming a constant acceleration a, when do we reach v_{drift}?

$$\xrightarrow{a = F/m} \xrightarrow{F = qE}$$

$$= \mu E = v_{drift} = a T = TF/m^* = TqE/m^* \rightarrow T = \mu m^*/q$$

(m^* = effective electron mass in crystal ~ 1.08 m_e at 4.2 K)

•
$$\mu \sim 0.14 \text{ m}^2/\text{Vs}$$

• $\text{m}^* \sim 1.08 \times 9.11 \times 10^{-31} \text{ kg}$
• $q = 1.6 \times 10^{-19} \text{ C}$

For fun:

How many silicon atoms does the electron pass by before it reaches drift speed? The distance depends on E: $c = E m u^2 / (2g) \approx 0.02 \mu m$ for E=0 EV//µm

s = E m $\mu^2/$ (2q) \sim 0.03 μm for E=0.5V/ μm

With the lattice constant of Si = 5.4307Å = $5.43 \times 10^{-4} \mu$ m, this are ~55 atoms.

T = 0.86 ps = 'instantaneous'

Velocity Saturation

Reference picture of drift velocity (from Sze):



Parameterization

Describe µ[E,T] with a fit to measured data

(C. Canali, G. Majni, R. Minder. and G. Ottaviani, "Electron and Hole Drift Velocity Measurements in Silicon and their Empirical Relation to Electric Field and Temperature", IEEE Trans. on Electron. devices, Nov. 1975, vol. 22, issue 11, pp. 1045-1047)

Parameterization:
$$\mu = \frac{v_{\rm s}/E_{\rm c}}{\left[1 + (E/E_{\rm c})^{\beta}\right]^{1/\beta}}$$
 (see pixel book)

Electrons:

- $V_s = 1.53 \times 10^9 \text{ T}^{-0.87} \text{ cm/s}$
- $E_c = 1.01 \text{ T}^{1.55} \text{ V/cm}$

•
$$\beta = 2.57 \times 10^2 \, \mathrm{T}^{0.66}$$

Holes:

- $V_s = 1.62 \times 10^8 \text{ T}^{-0.52} \text{ cm/s}$
- $E_c = 1.24 \text{ T}^{1.68} \text{ V/cm}$

•
$$\beta = 0.46 \text{ T}^{0.17}$$



Comparison to Sze (Overlay of previous formula)



Further simplification of Fit @ 300K

- Simpler Formulae for faster calculation
- Use new Units: $ns/\mu m/V$ ([E] = V/ μm , [v] = $\mu m/ns$)



Comparisons show simple formula vs. original formula@300K, x:Field in V/um, y: v in μ m/ns

How Relevant?

- Approximate field in Sensor:
 - 100V / 300µm → E = 0.3 V/µm
 - 300V / 300µm → E = 1 V/µm
- just at depletion significant overdepletion

• \rightarrow significant effect



Typical Value for Drift Time

- d = 300 µm = 0.03 cm detector thickness
- V = 100 V
- µ = 1400 cm²/Vs
- depletion voltage
 - ~ mobility of electrons

• v = μ E $\approx \mu$ V / d **approximation**! E is not constant! = 1400 cm²/Vs × 3333 V/cm = 4.7 × 10⁶ cm/s = 47 µm/ns

 During the drift time T ~ d² / μV, the charge cloud becomes larger by diffusion.

Calculate diffusion through full thickness:

$$\sigma = \sqrt{2 D T} = \sqrt{2 D \frac{d^2}{\mu V}} = d\sqrt{\frac{2 U_{Th}}{V}}$$

- (when using Einstein's equation $\frac{D}{\mu} = \frac{kT}{q} = U_{Th} \approx 26 \,\mathrm{mV}$)
- This is the same for electrons and holes!
- Numerical value:

$$\sigma = 300 \,\mu\mathrm{m} \sqrt{\frac{52 \,\mathrm{mV}}{100\mathrm{V}}} \approx 6.8 \,\mu\mathrm{m}$$

 $FWHM = 2\sqrt{2\ln 2}\sigma \approx 2.355\sigma = 16 \,\mu\text{m}$ (for a Gauss Distribution)



SIGNAL INDUCTION (SIGNALS FROM MOVING CHARGES)





- When charge Q is moving between conductors, when is the signal 'seen' (as charge) at the electrodes?
 - a) when Q reaches the electrodeb) immediately when Q moves
- Consider charge between two conductors:



Induced charge on S₁ / S₂ depends on the position

Two electrodes

- Voltage at electrodes is U, potential distribution is $\Phi(\vec{x})$
- Moving charge q by \vec{dx} changes potential energy by

$$dE_{pot} = q \, \vec{\nabla} \Phi(\vec{x}) \, \cdot \vec{dx}$$

The energy of the capacitor must change by this:

$$dE_{cap} = d\left(\frac{Q^2}{2C}\right) = \frac{QdQ}{C} = UdQ$$

- Energy conservation requires dE_{part} = dE_{cap}
- → The induced charge dQ on the capacitor is $dQ = dE_{cap} / U = dE_{part} / U = q \nabla(\Phi / U) dx$
- This dQ is independent of U (because $\Phi \sim U$)
 - In parallel plate cap with $\Phi(x) = U x / d \rightarrow \nabla(\Phi / U) = 1/d = const$
- When q drifts the whole way, the total charge is Q = ſdQ = a / U ſ ∇Φ dx = a

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- Consider general arrangement of N electrodes
- We want to know the signal on one electrode i when a charge is moved from A → B



- Ramo's theorem (1938):
 - 1. Calculate the solution of the Laplace equation $\Phi_W(x)$ for
 - $V_i = 1V$ and all other electrodes = 0V
 - 2. The charge induced on i is $\Phi_W(B) \Phi_W(A)$.
 - 3. The current is $j = \mathbf{v}(A) \nabla \Phi_{W}(A)$

Derivation of this

- Several Methods
 - Energy arguments
 - Green's Function
 - Gauss' Law
- See Spieler's Book, for instance...

- Weighting Field and real field (causing drift) are different!
- Weighting potential can be calculated numerically solving the Laplace equation
 - In one dimension, this is $d^2\Phi(x)/dx^2 = 0$
 - If space is discretized, i.e. $\Phi(x) \rightarrow \Phi_i$, then $d\Phi/dx = (\Phi_{i+1} - \Phi_i) / \Delta x$ $d^2\Phi/dx^2 = [(\Phi_{i+1} - \Phi_i) / \Delta x - (\Phi_i - \Phi_{i-1}) / \Delta x] / \Delta x$ $= (\Phi_{i+1} + \Phi_{i-1} - 2 \Phi_i) / \Delta x^2$
- The Laplace equation becomes $\Phi_i = (\Phi_{i+1} + \Phi_{i-1})/2$. i.e. Field values must be the average of the neighbors.
- This also works in 2 or 3 dimensions.
- Solution can be found iteratively
- See Program

How do solutions of Laplace's Equation look like?

• Center = Average of 4 neighbors: $\Phi_{i,j} = \frac{1}{4} (\Phi_{i-1,j} + \Phi_{i+1,j} + \Phi_{i,j-1} + \Phi_{i,j+1})$





| Constant: | 1 | 1 | 1 | | 0 | 0 | 0 | | | |
|------------------|----|----|----|---|----|---|----|----|----|---|
| | 1 | 1 | 1 | | 0 | 0 | 0 | | | |
| | 1 | 1 | 1 | | 0 | 0 | 0 | | | |
| | | | | | | | | | | |
| Linear Gradient: | 1 | 1 | 1 | | -1 | 0 | 1 | 0 | 1 | 2 |
| | 0 | 0 | 0 | | -1 | 0 | 1 | -1 | 0 | 1 |
| | -1 | -1 | -1 | | -1 | 0 | 1 | -2 | -1 | 0 |
| | | | | - | | | | | | |
| Saddle | 0 | -1 | 0 | | -1 | 0 | 1 | | | |
| | 1 | 0 | 1 | | 0 | 0 | 0 | | | |
| | 0 | -1 | 0 | | 1 | 0 | -1 | | | |

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Plot Lösungen in 3D

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Weighting Potential: Direct Calculation

- For 2D problems conformal mappings can be used to transform a geometry to another geometry.
- If the initial potential solves the Laplace Equation in the 'old' geometry, then Laplace's Equation is also fulfilled by the transformed potential in the new geometry.
- If (x,y) are considered as Real- and Imaginary part of a complex number z = x + i y, then any (complex) function f(z) = u(z) + i v(z) is a conformal mapping.
- Therefore, the problem is reduced to finding the correct complex transformation function

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Example for a Conformal Mapping



Weighting Potential of Strips

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Weighting Field for narrow strips

- a = 0.2
- See Mathematica



Superposition of all Weighting Potentials

• Superposition of Φ s of all strips \rightarrow parallel plate Potential



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Signals on Strip & Neighbor

- Strip sees increasing current
- Neighbor sees bipolar current
- See Applet



- Most charge is induced when charge is CLOSE
- Trapped (stuck) charges do not contribute much signal!

Signal in Parallel Plate Detector (no W-Potential!)

- For **parallel plate**, signals on both sides are **identical**!
- Signals from single charges & tracks quite different



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Signals in Strip Detector (\rightarrow Applet & FieldProgram)

- Electrons and holes have different speed
- Their contributions (for strips) are very different
- Total charge (no trapping!) is same on both sides!



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SIGNAL RECONSTRUCTION

- Consider very narrow signal
- Only one strip is hit
- Reconstructed position = strip center, error = offset in strip





- Consider 'Box' Signals for simplicity
- When 2 strips are hit \rightarrow reconstruct at edge \rightarrow small error



• Minimum Error for b = p/2. Error becomes half: $\sigma = \frac{1}{2} p/\sqrt{12}$

Example for 'Box' Signals

- Shallow Incidence
- Signal width z_{signal} depends on hit position z_{hit} and sensor thickness D
- Cross section of sensor:



- In this geometry, wider strips for large z are best!
- (Note that signals on neighbor pixels are not correlated!)

Reconstruction of Wide signals

- With signal distributed over many strips, can calculate center of gravity
- But: too wide signal (with constant amplitude)
 - → signal per strip gets small
 - → NOISE on strips degrades reconstruction
- Where is the optimum?



Limits in Spatial Resolution from Noise (1)

- Signal at position \vec{x} is distributed over N strips at \vec{x}_i
- Signal on i-th strip is $S_i(\vec{x})$
- Sum of all signals is normalized to 1:

$$\sum S_{i} = 1$$
 1

Assume we can perfectly reconstruct position as center of gravity:

$$\vec{x} = \frac{\sum S_{i}\vec{x}_{i}}{\sum S_{i}} = \sum S_{i}\vec{x}_{i}$$

- Now assume noise n_i on all strips
- Reconstructed position is now:

$$\vec{x}_{\rm rek}(\vec{x}) = \frac{\sum (S_{\rm i} + n_{\rm i})\vec{x}_{\rm i}}{\sum (S_{\rm i} + n_{\rm i})} = \frac{\vec{x} + \sum n_{\rm i}\vec{x}_{\rm i}}{1 + \sum n_{\rm i}}$$

This becomes (Taylor Expansion of Denominator):

$$\vec{x}_{\rm rek}(\vec{x}) = \frac{\vec{x} + \sum n_{\rm i}\vec{x}_{\rm i}}{1 + \sum n_{\rm i}} = \left(\vec{x} + \sum n_{\rm i}\vec{x}_{\rm i}\right) \left(1 - \sum n_{\rm i} + \mathcal{O}(n^2)\right)$$

The Error is therefore:

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$$\vec{x}_{\mathrm{err}}(\vec{x}) = \sum_{i} n_{\mathrm{i}}(\vec{x}_{\mathrm{i}} - \vec{x}) + \mathcal{O}(n^2).$$

We need the standard deviation:

$$\sigma_{\mathrm{err}}^2 = \langle \vec{x}_{\mathrm{err}}^2 \rangle - \langle \vec{x}_{\mathrm{err}} \rangle^2$$



$$= \sum_{i,j} \langle n_{i}n_{j} \rangle \langle (\vec{x}_{i} - \vec{x})(\vec{x}_{j} - \vec{x}) \rangle + \langle \mathcal{O}(n^{3}) \rangle$$
$$= \sigma_{n}^{2} \cdot \sum_{i} \langle (\vec{x}_{i} - \vec{x})^{2} \rangle + \mathcal{O}(\sigma_{n}^{3})$$

where we have used $\langle n_{\rm i} n_{\rm j}
angle = \delta_{ij} \cdot \sigma_{\rm n}^2$ for uncorrelated noise

If we chose the origin such that

$$\sum_{i} \vec{x}_{i} = \vec{0}$$

then this simplifies to:

$$\sigma_{\rm err}^2 = \sigma_{\rm n}^2 \left(\sum_{i=1}^N \vec{x}_i^2 + N \langle \vec{x}^2 \rangle \right) + \mathcal{O}(\sigma_{\rm n}^3).$$

The Shape of the noise distribution is only a small effect

3

Effect of Noise Distribution

- Various noise distributions can be treated by using higher moments
- Possible noise shapes
 - Gaussian Noise
 - 'Box' Noise
 - Noise from 50 Hz (sine) pickup
 - Theoretical limit of two delta peaks
- Effects are very small
- Formula: See exercise....

Example: Strips

- Consider two strips at $x_1 = -a/2$ and $x_2 = +a/2$
- Signals for a hit at x are

$$S_1(x) = (x_2 - x)/a$$
 and $S_2(x) = (x + x_2)/a$

• 1, 2 and 3 are fulfilled:

S₁ + S₂ = 1; x₁ S₁ + x₂ S₂ = x; x₁ + x₂ = 0 • We get $\left(\frac{\sigma_{\text{err}}}{\sigma_{\text{n}}}\right)^2 \approx x_1^2 + x_2^2 + \frac{2}{a} \int_{x_1}^{x_2} x^2 dx = \frac{2}{3} a^2$

• Or
$$\sigma_{
m err} = 0.816 \cdot a \cdot \sigma_{
m n}$$

• For $\sigma_n = 0.1$ (Signal/Noise = 10), resolution = 8% \cdot a

- Come back to center of gravity method
- Question:

What is the **theoretical limit** for a strip structure with **no noise** (i.e. the best we can do with this method)?

• We expect:

- Small error for wide signals
- $a/\sqrt{12}$ for narrow signals
- The following derivation is not found in books!
- Assumptions:
 - Charge cloud has a *symmetric* shape f(x), i.e. f(x) = f(-x)
 - f(x) is normalized, i.e. integral is 1
 - Strip pitch = width is a.

Reconstruction by Center of Gravity ('Centroid')



Divide Staircase in sym. / asym. parts $(0 < x_c < a/2)$



$$(\mathbf{x}) = m \sum Box_a (\mathbf{x} + \mathbf{x}_c - ma)$$

_eft edge:
$$-a/2 = x + x_c - ma \Rightarrow x = ma - a/2 - x_c$$



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Theoretical Limit of Centroid method

- Integral of asymmetric part is zero (f symmetric)
- We are left with

$$\begin{aligned} x_{\rm rek}(x_{\rm c}) &= a \int_{-\infty}^{\infty} f(x) g_{\rm sym}(x) dx \\ &= \frac{a}{2} - \frac{a}{2} \int_{-\infty}^{\infty} f(x) \sum_{m=-\infty}^{\infty} \operatorname{Rect}_{\mathrm{a}-2\mathrm{x}_{\rm c}}(x-ma) dx \\ &= \frac{a}{2} - \frac{a}{2} \int_{-\infty}^{\infty} f(x) \cdot \left[\operatorname{Rect}_{\mathrm{a}-2\mathrm{x}_{\rm c}}(x) \star \operatorname{comb}_{a}(x)\right] dx \end{aligned}$$

To solve this, move to Fourier Space with

$$\mathcal{F}[f(x)] = \tilde{f}(k) := \int_{-\infty}^{\infty} f(x) e^{-2\pi i k x} dx \quad \text{so that} \quad f(x) = \int_{-\infty}^{\infty} \tilde{f}(k) e^{2\pi i k x} dk$$

We can use

 $\int a(x) b(x) dx = \int \tilde{a}(k) \tilde{b}(k) dk$ and $\mathcal{F}[a \star b] = \mathcal{F}[a] \cdot \mathcal{F}[b]$ for real valued functions a, b

Integral in Fourier Space

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For very small f(x), the Fourier Transform ~f(..) goes → 1
 We get the Fourier Series of a saw tooth, as expected

Sigma of Reconstruction Error

$$\sigma_{\rm rec}^2 = \frac{1}{a} \int_{-a/2}^{a/2} x_{\rm err}^2(x_{\rm c}) \, dx_{\rm c}$$

$$= \frac{a}{\pi^2} \sum_{n,m=1}^{\infty} \frac{(-1)^{n+m}}{nm} \tilde{f}\left(\frac{n}{a}\right) \tilde{f}\left(\frac{m}{a}\right) \int_{-a/2}^{a/2} \sin \frac{2\pi n x_{\rm c}}{a} \sin \frac{2\pi m x_{\rm c}}{a} \, dx_{\rm c}$$

$$= \frac{a}{\pi^2} \sum_{n,m=1}^{\infty} \frac{(-1)^{n+m}}{nm} \tilde{f}\left(\frac{n}{a}\right) \tilde{f}\left(\frac{m}{a}\right) \frac{a}{2} \cdot \delta_{n,m}$$

$$\sigma_{\rm rec}^2 = \frac{a^2}{2\pi^2} \sum_{m=1}^{\infty} \frac{1}{m^2} \tilde{f}^2\left(\frac{m}{a}\right).$$

For a point like signal with $\tilde{f}(k) \to 1$, this leads to

$$\sigma_{\rm rec}^2 = \frac{a^2}{2\pi^2} \sum_{m=1}^{\infty} \frac{1}{m^2} = \frac{a^2}{12}$$

or $\sigma_{\rm rec} = a/\sqrt{12}$ as expected. Silicon Detectors - Signals

$\hfill \mbox{For a Gaussian signal with width } \sigma$

$$G(x) = \frac{1}{\sqrt{2\pi\sigma_s}} \exp\left(-\frac{x^2}{2\sigma_s^2}\right) \qquad \text{with} \qquad \tilde{G}(k) = \exp\left(-2\pi^2 k^2 \sigma_s^2\right)$$

we get

$$\tilde{\sigma}_{\rm rec}^2 = \frac{1}{2\pi^2} \sum_{m=1}^{\infty} \frac{e^{-4\pi^2 s^2 m^2}}{m^2}$$

- Here
$$\tilde{\sigma}_{
m rec}:=\sigma_{
m rec}/a$$
 and s = σ/a

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• Method is 'nearly perfect' when $\sigma > a/2$



- $\hfill\blacksquare$ Resolution for small σ is bad
- The infinite sum must be limited to reduce noise contributions. The choice is fairly arbitrary
- In real system, there is often a threshold (hits below this are not read out)
- The reconstructed amplitude is wrong (signals below threshold are lost)
- Broken pixels need special treatment



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Noise will degrade resolution for wide clusters

S/N = 40



 There is an optimum signal width σ = 0.4 a (This depends only weakly on noise)

S/N = 80

- (Normalized) Probability Density is given.
- Numerically: piecewise linear function (corner pairs (x_i, y_i))



Generate Random Number in [0..1], Use as y, look up x

A better approach...





Differences must be explained by noise



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Better (?) Approach...

- Assume a hit position x and amplitude a
- All differences between measurement and expectations must be explained by noise and threshold
- Even a **non-hit** (below threshold) gives information!
- Work in progress..
- Looks good (see plots). But complicated for 2D structures and real-world behavior (needs lookup tables)
- Stay tuned...